

Product Overview

NTMFS4983NF: Single N-Channel Power MOSFET 30V, 106A, 2.1mΩ

For complete documentation, see the data sheet.

Power MOSFET 30 V, 106 A, Single N-Channel, SO-8 FL

Features

- Integrated Schottky Diode
- Low $r_{DS(on)}$ to Minimize Conduction Loss
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- RoHS Compliant

Applications

- CPU Power Delivery
- Synchronous Rectification for DC-DC Converters
- Low Side Switching
- Telecom Secondary Side Rectification

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	$V_{(BR)DSS}$ Min (V)	V_{GS} Max (V)	$V_{GS(th)}$ Max (V)	I_D Max (A)	P_D Max (W)	$R_{DS(on)}$ Max @ $V_{GS} = 2.5$ V (mΩ)	$R_{DS(on)}$ Max @ $V_{GS} = 4.5$ V (mΩ)	$R_{DS(on)}$ Max @ $V_{GS} = 10$ V (mΩ)	Q_g Typ @ $V_{GS} = 4.5$ V (nC)	Q_g Typ @ $V_{GS} = 10$ V (nC)	C_{iss} Typ (pF)	Package Type
NTMFS4983NFT1G	0.4	Pb-free Halide free	Active	N-Channel	Single	30	20	2.3	106	3.13	-	3.1	2.1	25	22.6	3250	SO-8FL / DFN-5
NTMFS4983NFT3G	0.4009	Pb-free Halide free	Active	N-Channel	Single	30	20	2.3	106	3.13	-	3.1	2.1	25	22.6	3250	SO-8FL / DFN-5

For more information please contact your local sales support at www.onsemi.com.

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